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January 2016

# FQP3P50

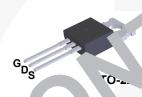
# P-Channel QFET® MOSFET -500 V, -2.7 A, 4.9 Ω

# **Description**

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Toted DC motor control, and variable switching power applications.

### **Features**

- -2.7 A, -500 V,  $R_{DS(on)}$  = 4.9  $\Omega$  (Max.) @  $V_{GS}$  = -10 V,  $I_D = -1.35 A$
- Low Gate Charge (Typ. 18 nC)
- · Low Crss (Typ 9.5 pF)





# Absolute Max num Tatings To = 20 C unless of however noted

Symbol	Parameter	FQP3P50	Unit
V <sub>DSS</sub>	□ rain ⊃urce Voltage	-500	V
	Current Continuous (T <sub>C</sub> = 25°C)	-2.7	А
	- Crinin ious (T <sub>C</sub> = 175°C)	-1.71	А
I <sub>DM</sub>	Drain Current - Fulsed (Note	1) -10.8	A
JS	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Puised Avalenche Energy (Note	2) 250	mJ
I <sub>AP</sub>	Avalanche Curi an' (Note	1) -2.7	A
Evs	Repetitive Avalanche Energy (Note	1) 8.5	mJ
dv/dt	Peal Diode Recovery dv/dt (Note	3) -4.5	V/ns
P <sub>D</sub>	Powe: Dissipation (T <sub>C</sub> = 25°C)	85	W
	- Derate above 25°C	0.68	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>I</sub>	Maximum lead temperature for soldering,	300	°C
'L	1/8" from case for 5 seconds	300	

# **Thermal Characteristics**

Symbol	Parameter	FQP3P50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.47	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP3P50	FQP3P50	TO-220	Tube	N/A	N/A	50 units

# **Elerical Characteristics**

 $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-500			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, Referenced to 25°C		0.42		V/°C
I <sub>DSS</sub>	Zoro Coto Voltago Proin Current	V <sub>DS</sub> = -500 V, V <sub>GS</sub> = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -400 V, T <sub>C</sub> = 125°C			-10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-,	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V		-	10	nA
		•				

# On Characteristics

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	T	-35.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, I_D = -1 - 5 \text{ A}$		- 39 7.9	Ω
9FS	Forward Transconductance	V <sub>DS</sub> = -50 V, , 35		2.35	S

# **Dynamic Characteristics**

-					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub>	25 V, V, = 0 V,	10 560	pF
Coss	Output Capacitance	f = 1.0	·Iz	70 >30	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		NV R	9.5 12	pF

# Switching Characterist's

t <sub>d(on)</sub>	Turn-On Delon Time $V_{DL} = -250 \text{ V}, v_D = -2.7 \text{ A}.$	7/	12	35	ns
t <sub>r</sub>	Turn-On se Time $R_G = 25 \text{ G}$ .		56	120	ns
t <sub>d(off)</sub>	Turn-Off Nay Tim		35	80	ns
t <sub>f</sub>	rurn-Off F <sub>c</sub> Tim (Note	4)	45	100	ns
$Q_g$	$V_{DS} = -4.00 \text{ V.} \cdot V_{D} = -2.7 \text{ A},$		18	23	nC
0.4	Gr'a-S ice Charge $V_{SS} = -10 \text{ V}$		3.6		nC
Q <sub>g</sub> ,	Gate-Drain Charge (Note	4)	9.2		nC

# ്ഥ-Source Diode Characteristics and Maximum Ratings

·s	Maximum Coli tinuous Drain-Cource Diode Forward Current		 	-2.7	Α
I <sub>SN</sub>	Maximum Pulsed Spain Source Diode Forward Current		 	-10.8	Α
V <sub>SD</sub>	Drain-Source Dicde Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -2.7 \text{ A}$	 	-5.0	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = -2.7 \text{ A,}$	 270		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$	 1.5	//	μС

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 62 mH, I $_{AS}$  = -2.7 A, V $_{DD}$  = -50 V, R $_{G}$  = 25  $\Omega$ , starting T $_{J}$  = 25°C. 3. I $_{SD}$   $\leq$  -2.7 A, di/dt  $\leq$  200 A/ $\mu s$  , V $_{DD}$   $\leq$  BV $_{DSS}$ , starting T $_{J}$  = 25°C.
- 4. Essentially independent of operating temperature.

# **Typical Characteristics**

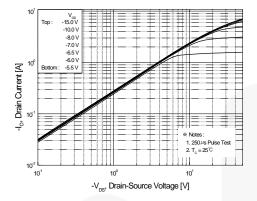


Figure 1. On-Region Characteristics

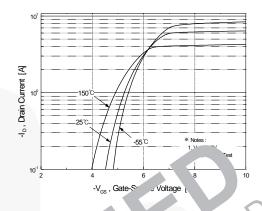
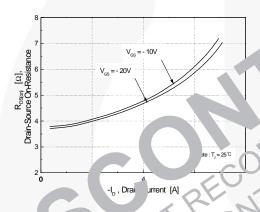


Figure 2. 1 nst. Char ceristics



n.gure 3 On-Resistance Variation vs. Pro: Gurrent and Gate Voltage

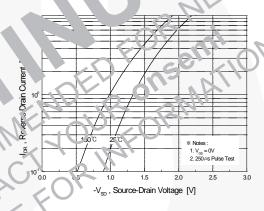


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

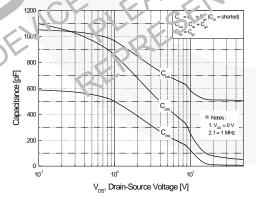


Figure 5. Capacitance Characteristics

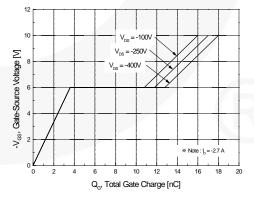


Figure 6. Gate Charge Characteristics

# Typical Characteristics (Continued)

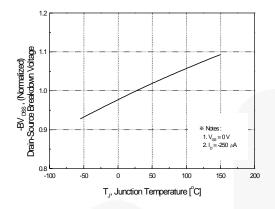
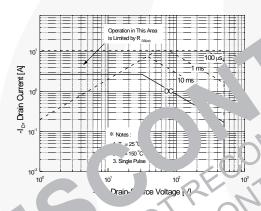


Figure 7. Breakdown Voltage Variation vs. Temperature



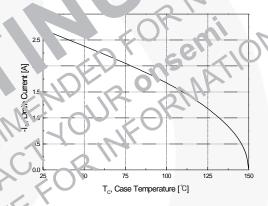


Figure 9. / aximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

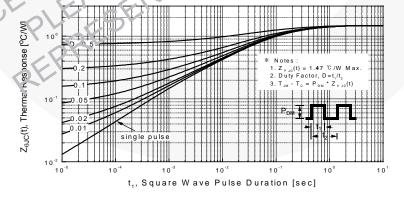


Figure 11. Transient Thermal Response Curve

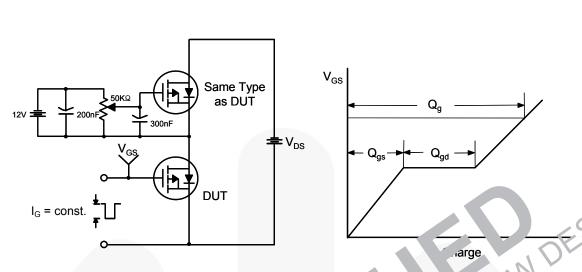


Figure 12. Gate Charge Test Circuit & Vave. \*m

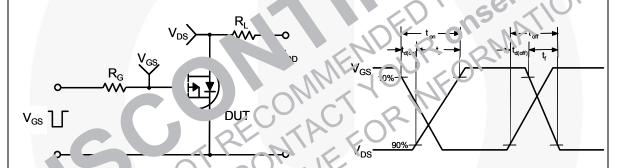


Figure 13. Resistive Switching Test Circuit & Waveforms

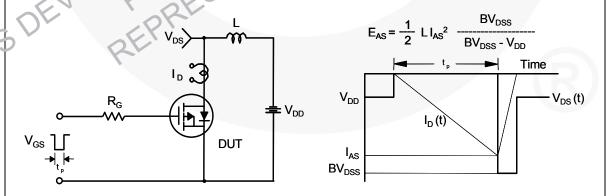
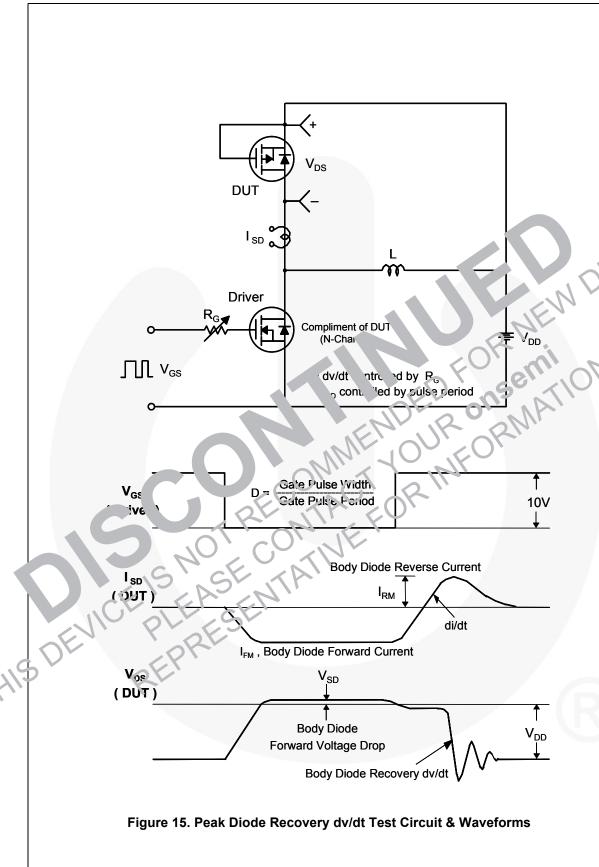


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**

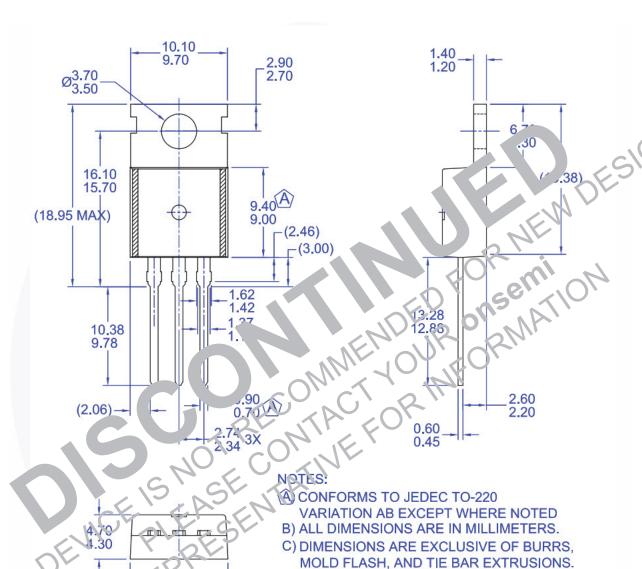


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

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